TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W08F, TC7W08FU

DUAL 2-INPUT AND GATE

The TC7W08 is a high speed C²MOS 2-INPUT AND GATE fabricated with silicon gate C²MOS technology.

It achives the high speed operation similar to equivalent LSTTL while maintaining the C²MOS low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

•	High Speed	 $t_{pd} = 6ns (Typ.)$	at
		Усс = 5V	

• Low Power Dissipation
$$I_{CC} = 1\mu A$$
 (Max.) at $Ta = 25^{\circ}C$

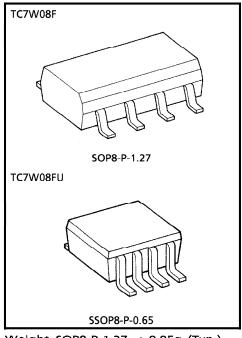
$$= 28\% \text{ V}_{CC} \text{ (Min.)}$$

• Symmetrical Output Impedance ...
$$|OH| = IOL = 4mA$$

(Min.)

• Balanced Propagation Delays $t_{pLH} = t_{pHL}$

Wide Operating Voltage Range ... V_{CC} (opr) = 2~6V

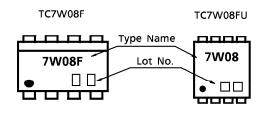


Weight SOP8-P-1.27 : 0.05g (Typ.) SSOP8-P-0.65 : 0.02g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	-0.5~7	V
DC Input Voltage	V _{IN}	-0.5~V _{CC} + 0.5	V
DC Output Voltage	Vout	-0.5~V _{CC} + 0.5	V
Input Diode Current	ΙΚ	± 20	mA
Output Diode Current	^I ок	± 20	mA
DC Output Current	IOUT	± 25	mΑ
DC V _{CC} /Ground Current	lcc	± 25	mA
Power Dissipation	PD	300	mW
Storage Temperature	T _{stg}	- 65~150	°C
Lead Temperature (10s)	TL	260	°C

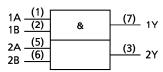
MARKING



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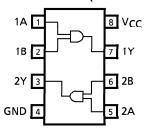
LOGIC DIAGRAM



TRUTH TABLE

А	В	Υ
L	L	L
L	Н	L
Н	L	Ĺ
Н	Н	Н

PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	2~6	V
Input Voltage	VIN	0~V _{CC}	٧
Output Voltage	Vout	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C
		$0\sim1000 \ (V_{CC}=2.0V)$	
Input Rise and Fall Time	t _r , t _f	$0 \sim 500 \ (V_{CC} = 4.5V)$	ns
		$0 \sim 400 \ (V_{CC} = 6.0V)$	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION V			Ta = 25°C			Ta = -4	0∼85°C	UNIT
CHARACTERISTIC	STIVIBUL			Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High Loyal	VIH			2.0	1.5	_	_	1.5	_	
High-Level Input Voltage			_	4.5	3.15	_	—	3.15	_	V
input voitage				6.0	4.2	_	—	4.2	_	
Low-Level				2.0	_	_	0.5		0.5	
Input Voltage	VIL		_	4.5	<u> </u>	—	1.35	_	1.35	V
input voitage				6.0	_	_	1.8	1	1.8	
				2.0	1.9	2.0	_	1.9	_	
I I i ala I accal	Voн		$I_{OH} = -20\mu A$	4.5	4.4	4.5	—	4.4	_	
High-Level		VIN = VIH		6.0	5.9	6.0	—	5.9	_	V
Output Voltage			I _{OH} = -4mA	4.5	4.18	4.31	—	4.13	_	
			$I_{OH} = -5.2 \text{mA}$	6.0	5.68	5.80	_	5.63	_	
	1 VAI 1	V _{IN} = V _{IH} or V _{IL}		2.0	_	0.0	0.1	_	0.1	
Lave Lavel			$I_{OL} = 20 \mu A$	4.5	_	0.0	0.1	_	0.1	
Low-Level				6.0	_	0.0	0.1	-	0.1	V
Output Voltage			I _{OL} = 4mA	4.5	_	0.17	0.26		0.33	
			$I_{OL} = 5.2 \text{mA}$	6.0	_	0.18	0.26	-	0.33	
Input Leakage Current	IIN	V _{IN} = V _{CC} o	or GND	6.0	_		± 0.1	_	± 1.0	
Quiescent Supply Current	^l cc	$V_{IN} = V_{CC}$	or GND	6.0	_	_	1.0	_	10.0	μΑ

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, $V_{CC} = 5V$, Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Т	UNIT		
CHARACTERISTIC	STIVIBUL	TEST CONDITION	MIN.	TYP.	MAX.	UNII
Output Transition	tTLH			4	۰	20
Time	tTHL	_		4	°	ns
Propagation Delay	t _{pLH}			6	12	20
Time	t _{pHL}	_		O	12	ns

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

CHARACTERISTIC	SYMBOL	DL TEST CONDITION		Ta = 25°C			Ta = -4	UNIT	
CHARACTERISTIC	3 I WIBOL	TEST CONDITION		MIN.	TYP.	MAX.	MIN.	MAX.	OWIT
Output Transition	t		2.0	_	25	75	_	95	
	t _{TLH}	_	4.5	<u> </u>	7	15	_	19	ns
Time	[†] THL	HL	6.0	 	6	13	_	16	
Drangation Dalou	4		2.0	_	27	75	_	95	
Propagation Delay	t _{pLH}	_	4.5		8	15	-	19	ns
Time	t _{pHL}		6.0	—	7	13	—	16	
Input Capacitance	CIN	_		_	5	10	_	10	
Power Dissipation Capacitance	C _{PD}	(Note 1)		_	19	_	_	_	pF

Note 1 : CpD is defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

Average operating current can be obtained by the equation hereunder. $|CC(opr)| = CPD \cdot VCC \cdot f|N + |CC|/2$ (per gate)